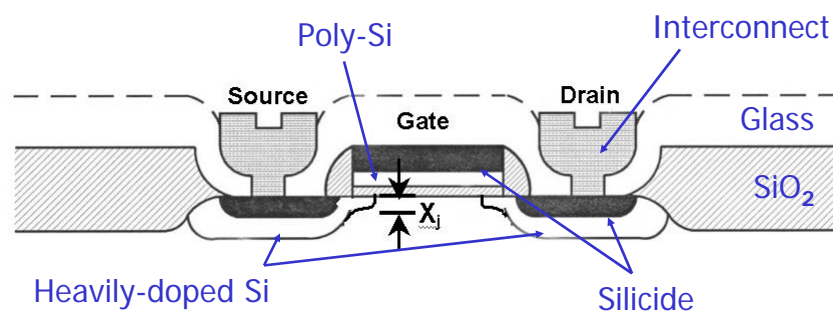


An Interdisciplinary Lecture Course for Microelectronics Fabrication


1

MOSFET Schematic



- Hundreds of process steps
- Many materials
- Some components are nanoscale: finite-size effects

2




International Technology Roadmap for Semiconductors

	1999	2001	2004	2007	2010	2013
DRAM half-pitch (nm)	180	130	90	65	45	32
Transistors/chip at production (millions)	61	97	193	386	773	1546
MPU cost/function (μcents/transistor)	120	60	30	15	5.3	1.9

- Rapid scaling requires skilled workforce for processing
 - Interdisciplinary, flexible

3

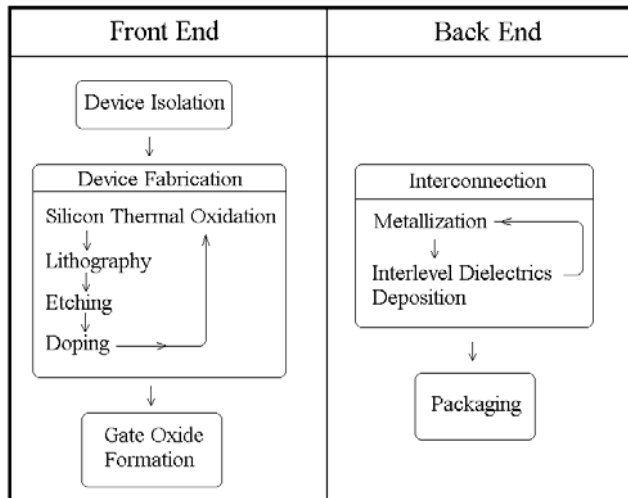


Employment Patterns

- Typical US fab employs:
 - 25-30% chemical engineering
 - 25-30% electrical engineering
 - Remainder: materials science, mechanical eng, physics...
- Distribution of training differs outside US
- Fast-moving but high capitalization
 - Profit margins squeezed, patterns shifting
 - Market cycles
 - Time-to-market critical
- Technical staff must have working knowledge beyond their formal disciplinary training

4

Process Flow Schematic



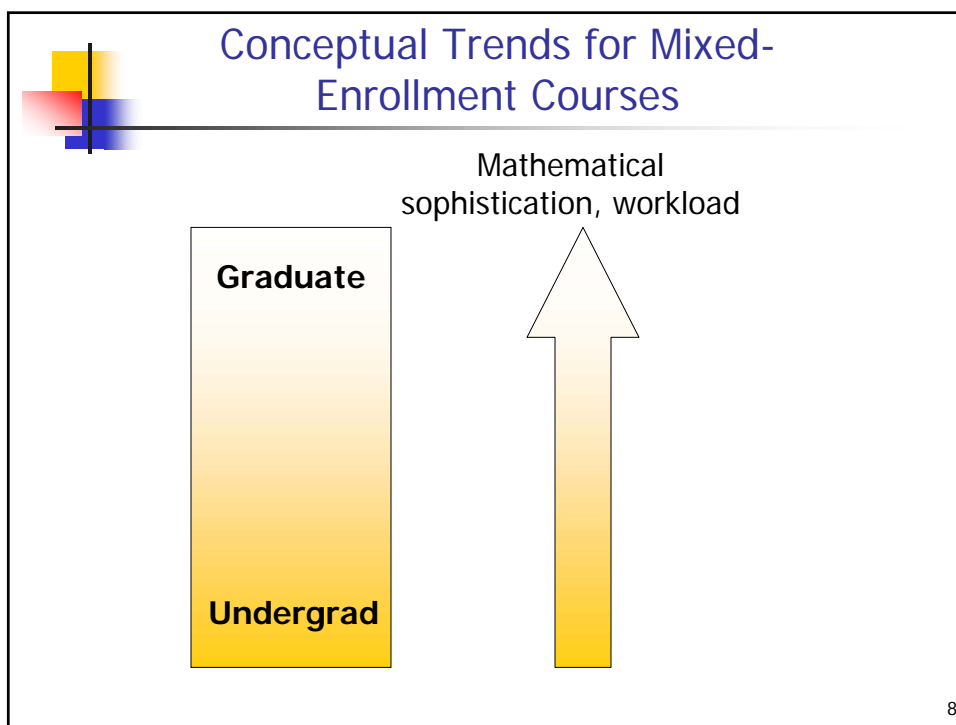
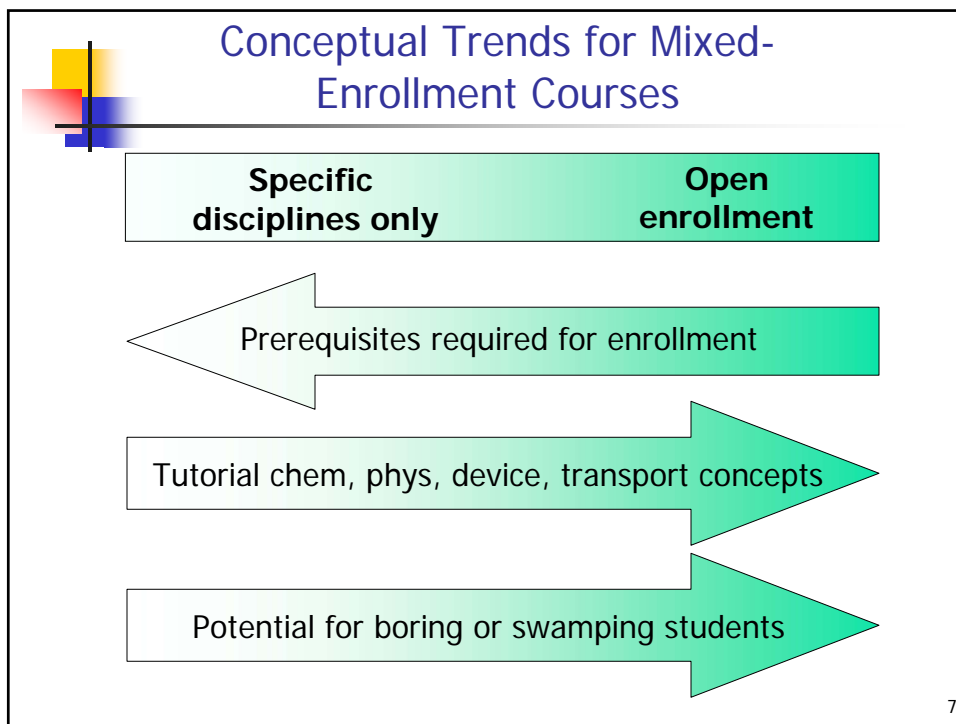
- Hundreds of steps
- Unit-ops concepts:
 - Lithography
 - Doping
 - Deposition
 - Etching
 - Cleaning/polishing
- Much chemistry, transport

5

Student Enrollment

- Advantages of mixed course enrollment
 - Gives tast of work environment in fab
 - Broadens student base to justify large investment
- Two dimensions to mixed enrollment:
 - Multiple disciplines
 - Electrical/microelectronics engineering
 - Chemical engineering
 - Materials science
 - Chemistry
 - Physics
 - Multiple degree levels
 - MS, PhD
 - Upper-level undergraduate

6

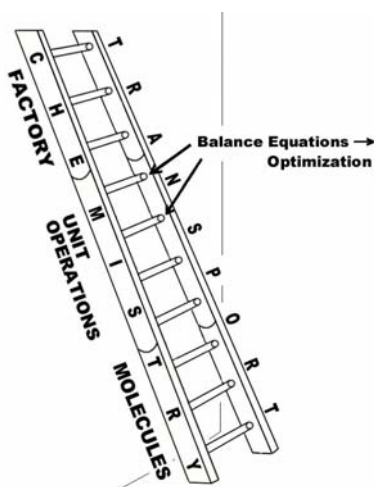


"Chemistry & Transport in Semiconductor Materials Synthesis"

- Broad audience
 - ChE, EE, Chemistry, Materials Sci
 - Grad & Undergrad
- ~24 students per offering
 - Eight groups of 3 (mixed-discipline)
- Limited number of in-depth experiments
 - Closely coupled to computational modeling
- Original course funded by AMAT, Intel, Illinois Board of Higher Education, 4 campus units

9

Purposes of Lecture Courses



- Transfer specific facts
 - Technology details
 - Mathematical methods
- Offer an ordered framework for facts: knowledge
 - Unit operations \leftrightarrow process flow
 - Unity of form for balance eqns in mass, energy, momentum

Rev Chem Eng, **18** (2001) 1. 10

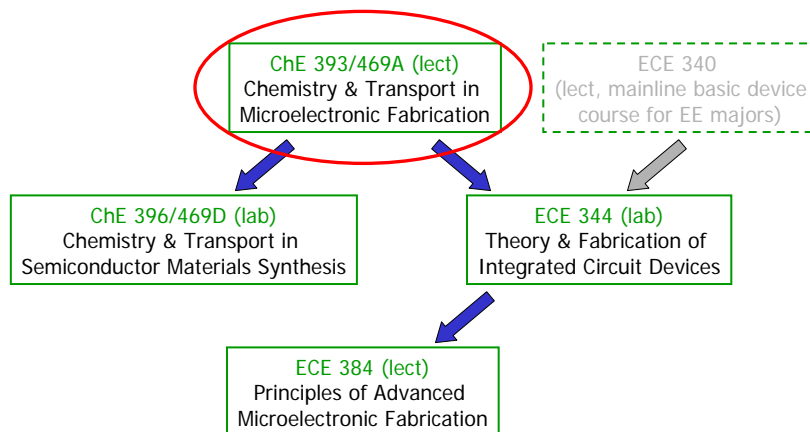
UIUC: "Chemistry & Transport in Microelectronic Processing"

- Lecture course, 70+ students per offering
- Broad audience
 - ChE, EE, Chemistry, Materials Sci
 - Grad & Undergrad
- 2-week intro to semiconductor physics, devices
- Subjects ordered by increasing sophistication of mathematical governing equations

11

Informal Option in Processing at UIUC

- Up to 4 elective courses in chem eng, electrical eng
- Prerequisites kept minimal



12



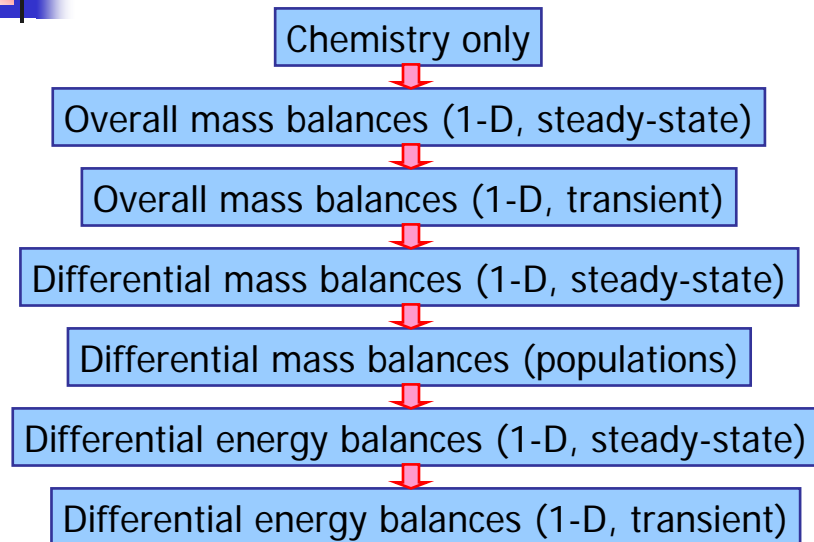
Course Structure

- Begin with 2 weeks of semiconductor device physics
 - More than this bores EE students
- Continue with lithography physics/chemistry
- Order remaining processing subjects by increasing sophistication of:
 - Mathematics
 - Conceptual difficulty of balance equations

13



Conceptual Ordering of Processing Topics



14



Lectures 1-9

Lect. No.	Topics	Underlying Concepts
1 2	<ul style="list-style-type: none">• Industry history• SIA Roadmap• Semiconductor materials	Overall perspective
3 4 5	<ul style="list-style-type: none">• Semiconductor physics• pn junctions• Field effects	Solid state physics
6 7	<ul style="list-style-type: none">• Lithography	Optics
8 9	<ul style="list-style-type: none">• Etching (wet)	Buffers Electrochemistry

15



Lectures 10-13

Lect. No.	Topics	Underlying Concepts
10	<ul style="list-style-type: none">• Etching (dry)	Plasma phenomena
11	<ul style="list-style-type: none">• Etching (dry)	Plasma phenomena
12	<ul style="list-style-type: none">• Physical vapor deposition	Sputtering physics Process control
13	<ul style="list-style-type: none">• Rapid thermal processing	Rate selectivity Process control
	Microelec. Lab Tour	

16



Lectures 14-18

Lect. No.	Topics	Underlying Concepts
14 15 16 17	• Chemical vapor deposition	Surface kinetics Kinetics/gas transport Boundary layers Case study: TiSi_2
18	• Si oxidation	Rate-limiting steps Diffusion-rxn (differential mass balances, 1-D)

17



Lectures 19-22

Lect. No.	Topics	Underlying Concepts
19 20	• Si refining	Well-stirred reactors Differential mass balances on distributions
21	• Czochralski growth	Separations by crystallization Differential energy balances (1-D)
22	• Diffusional doping	Defect thermodynamics Transient diffusion equations

18



Lectures 23-26

Lect. No.	Topics	Underlying Concepts
23	• Diffusional doping	Defect thermodynamics Transient diffusion equations
24	• Ion implantation • Transient enhanced diffusion	Implantation physics Diffusion-rxn (3-D PDE's)
25	• Packaging	Electrochemistry 1-D heat transfer
26	• Factory-level issues	Process integration

19



Role of Modeling

- Simple, unsophisticated
 - Simple analytical
 - Rate selectivity
 - Deal-Grove model of oxidation
 - Easy-to-use software packages
 - For undergraduate, graduate students
- Sophisticated
 - Complex analytical
 - Transient enhanced diffusion
 - Spin coating
 - CVD with viscous flow
 - Dry etching with flow
 - For graduate students only

20



Lecture Course Challenges

- Initial investment of time (several years)
- Experienced staffing
- Setting proper pace, depth
- Creating faculty, student constituency



21



Techniques to Mitigate Challenges

- Engage faculty from several disciplines
 - Adds depth to presentation
 - Helps set appropriate pace, depth
 - Expands pool of students likely to enroll
 - Aids in staffing

22



Summary

- Lecture courses relatively easy to set up
 - Helps to have interdisciplinary faculty constituency
- Begin with a little device background
- Introduce processing concepts in order of increasing mathematical, conceptual difficulty
 - Balance between qualitative, mathematical content